

1N4153

FEATURES :

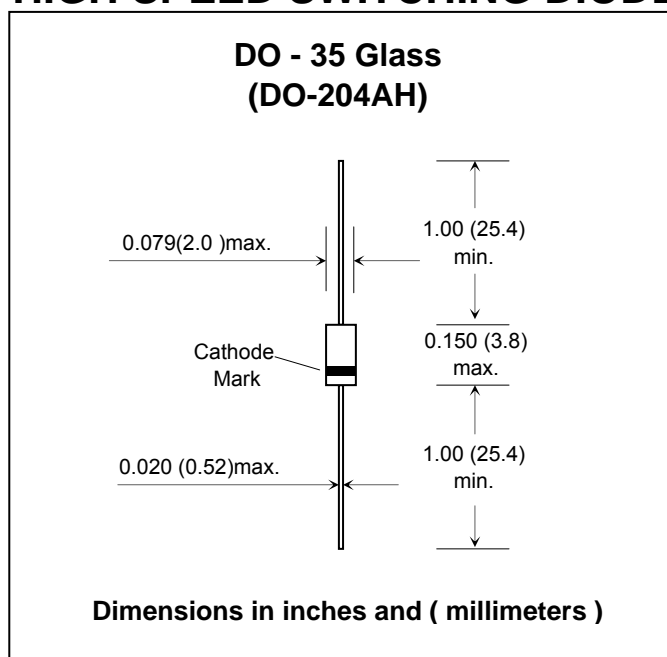
- High switching speed: max. 2 ns
- Peak reverse voltage: max. 75 V
- Pb / RoHS Free

MECHANICAL DATA :

Case: DO-35 Glass Case

Weight: approx. 0.13g

HIGH SPEED SWITCHING DIODE



Maximum Ratings and Thermal Characteristics (Rating at 25 °C ambient temperature unless otherwise specified.)

Parameter	Symbol	Value	Unit
Maximum Peak Reverse Voltage	V_{RM}	75	V
Maximum Continuous Forward Current	I_F	300	mA
Maximum Average Forward Current	$I_{F(AV)}$	150	mA
Maximum Peak Forward Current at $t = 1s$	I_{FSM}	0.25	A
Maximum Power Dissipation	P_D	500	mW
Maximum Junction Temperature	T_J	175	°C
Storage Temperature Range	T_{STG}	-65 to + 200	°C

Electrical Characteristics ($T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Reverse Current	I_R	$V_R = 50\text{ V}$	-	-	0.05	μA
		$V_R = 50\text{ V}, T_J = 150\text{ }^\circ\text{C}$	-	-	50	μA
Forward Voltage	V_F	$I_F = 50\text{ mA}$	-	-	0.88	V
Reverse Breakdown Voltage	$V_{(BR)R}$	$I_R = 5\text{ A (pulsed)}$	75	-	-	V
Diode Capacitance	C_d	$f = 1\text{ MHz}; V_R = 0$	-	-	2.0	pF
Reverse Recovery Time	T_{rr1}	$I_F = 10\text{ mA to } I_R = 10\text{ mA}$ to $I_R = 1\text{ mA}$	-	-	4	ns
	T_{rr2}	$I_F = 10\text{ mA to } V_R = 6\text{ V}$ $R_L = 100\ \Omega, I_R = 1\text{ mA}$	-	-	2	ns